



# **High-Voltage Switching Applications**

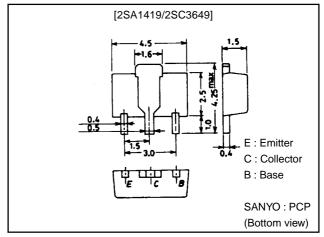
### **Features**

- · Adoption of FBET, MBIT processes.
- · High breakdown voltage and large current capacity.
- · Very small size making it easy to provide highdensity hybrid ICs.

# **Package Dimensions**

unit:mm

2038



(): 2SA1419

## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

| Parameter                    | Symbol           | Conditions   | Ratings     | Unit |
|------------------------------|------------------|--|-------------|------|
| Collector-to-Base Voltage    | VCBO             |  | (-)180      | V    |
| Collector-to-Emitter Voltage | VCEO             |  | (–)160      | V    |
| Emitter-to-Base Voltage      | V <sub>EBO</sub> |  | (-)6        | V    |
| Collector Current            | IC               |  | (-)1.5      | Α    |
| Collector Current (Pulse)    | ICP              |  | (-)2.5      | Α    |
| Collector Dissipation        | PC               |  | 500         | mW   |
|                              |                  | Moutned on ceramic board (250mm <sup>2</sup> ×0.8mm) | 1.5         | W    |
| Junction Temperature         | Tj               |  | 150         | °C   |
| Storage Temperature          | Tstg             |  | -55 to +150 | °C   |

### Electrical Characteristics at Ta = 25°C

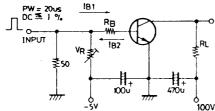
| Parameter                               | Symbol               | Conditions  |        | Ratings |        |      |  |
|---|----------------------|---|--------|---------|--------|------|--|
| Faiametei                               | Symbol               | Conditions  | min    | typ     | max    | Unit |  |
| Collector Cutoff Current                | ICBO                 | V <sub>CB</sub> =(-)120V, I <sub>E</sub> =0       |        |         | (–)1   | μΑ   |  |
| Emitter Cutoff Current                  | I <sub>EBO</sub>     | V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0         |        |         | (-)1   | μΑ   |  |
| DC Current Gain                         | h <sub>FE</sub> 1    | V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)100mA  | 100*   |         | 400*   |      |  |
|   | h <sub>FE</sub> 2    | V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)10mA   | 80     |         |        |      |  |
| Gain-Bandwidth Product                  | fT                   | V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA  |        | 120     |        | MHz  |  |
| Output Capacitance                      | C <sub>ob</sub>      | V <sub>CB</sub> =(-)10V, f=1MHz                   |        | (22)    |        | pF   |  |
|   |                      |   |        | 14      |        | pF   |  |
| Collector-to-Emitter Saturation Voltage | V <sub>CE(sat)</sub> | I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)50mA |        | (-200)  | (-500) | mV   |  |
|   |                      |   |        | 130     | 450    | mV   |  |
| Base-to-Emitter Saturation Voltage      | V <sub>BE(sat)</sub> | I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)50mA |        | (-)0.85 | (-)1.2 | V    |  |
| Collector-to-Base Breakdown Voltage     | V <sub>(BR)CBO</sub> | I <sub>C</sub> =(-)10μΑ, I <sub>E</sub> =0        | (–)180 |         |        | V    |  |
| Collector-to-Emitter Breakdown Voltage  | V <sub>(BR)CEO</sub> | I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞        | (–)160 |         |        | V    |  |
| Emitter-to-Base Breakdown Votage        | V <sub>(BR)EBO</sub> | I <sub>E</sub> =(-)10μA, I <sub>C</sub> =0        | (–)6   |         |        | V    |  |
| Turn-ON Time                            | ton                  | See specified Test Circuit.                       |        | (40)    |        | ns   |  |
|   |                      |   |        | 40      |        | ns   |  |
| Stotage Time                            | t <sub>stg</sub>     | See specified Test Circuit.                       |        | (0.7)   |        | μs   |  |
|   |                      |   |        | 1.2     |        | μs   |  |
| Fall Time                               | t <sub>f</sub>       | See specified Test Circuit.                       |        | (40)    |        | ns   |  |
|   |                      |   |        | 80      |        | ns   |  |

 $\mbox{\ast}$  : The 2SA1419/2SC3649 are classified by 100mA  $\mbox{h}_{FE}$  as follows :

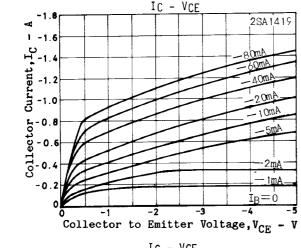
|                      | 100 | R | 200 | 140                            | S | 280 | 200 | Т | 400 |
|----------------------|-----|---|-----|--------------------------------|---|-----|-----|---|-----|
| Marking 2SA1419 : AE |     |   |     | h <sub>FE</sub> rank : R, S, T |   |     |     |   |     |

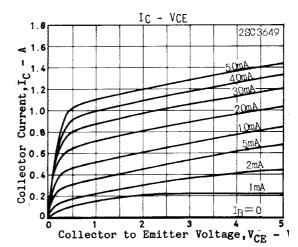
2SC3649 : CE

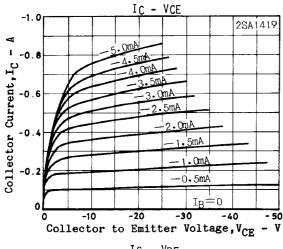
### **Switching Time Test Circuit**

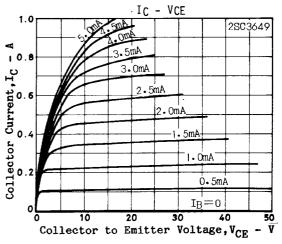


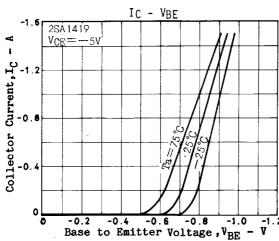
(For PNP, the polarity is reversed) Unit (resistance :  $\Omega$ , capacitance : F)

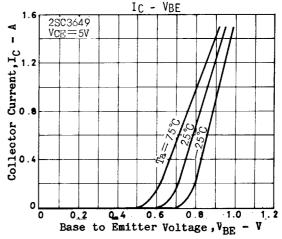


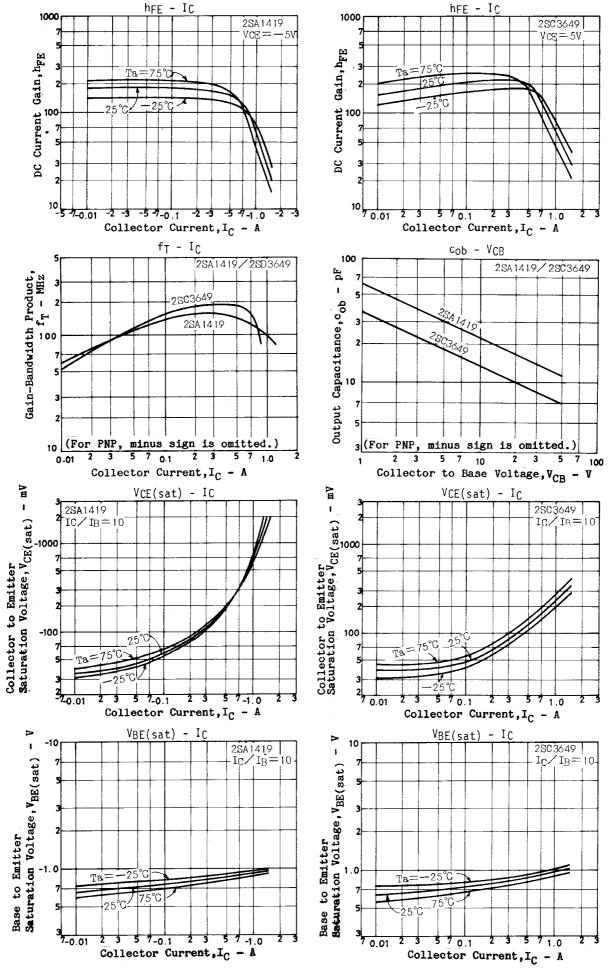




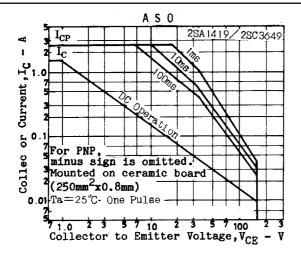


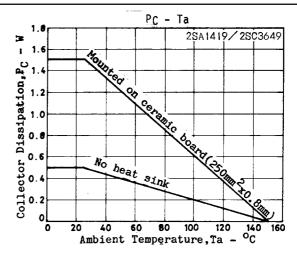






### 2SA1419/2SC3649





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